

2SB1299

Silicon PNP epitaxial planar type

For power amplification

Complementary to 2SD1273

■ Features

- High forward current transfer ratio h_{FE}
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

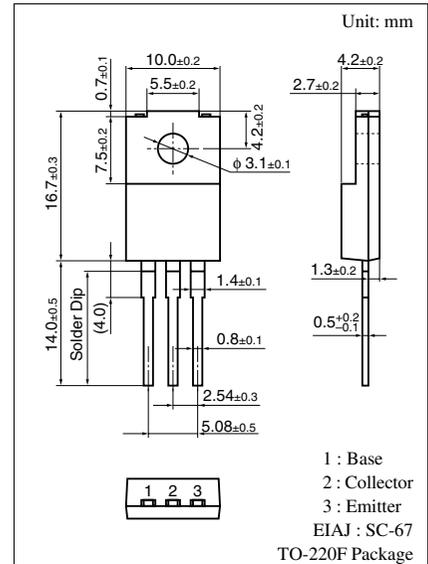
| Parameter | Symbol | Rating | Unit | |
|------------------------------|--------------------------|-------------|------------------|---|
| Collector to base voltage | V_{CBO} | -60 | V | |
| Collector to emitter voltage | V_{CEO} | -60 | V | |
| Emitter to base voltage | V_{EBO} | -6 | V | |
| Peak collector current | I_{CP} | -6 | A | |
| Collector current | I_C | -3 | A | |
| Base current | I_B | -1 | A | |
| Collector power dissipation | $T_C = 25^\circ\text{C}$ | P_C | 40 | W |
| | $T_a = 25^\circ\text{C}$ | | 2 | |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ | |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ | |

■ Electrical Characteristics $T_C = 25^\circ\text{C}$

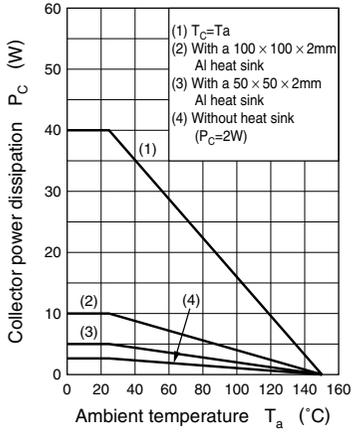
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---|---------------|---|-----|-----|------|---------------|
| Collector cutoff current | I_{CBO} | $V_{CB} = -60\text{ V}, I_E = 0$ | | | -100 | μA |
| | I_{CEO} | $V_{CE} = -40\text{ V}, I_B = 0$ | | | -100 | μA |
| Emitter cutoff current | I_{EBO} | $V_{EB} = -6\text{ V}, I_C = 0$ | | | -100 | μA |
| Collector to emitter voltage | V_{CEO} | $I_C = -25\text{ mA}, I_B = 0$ | -60 | | | V |
| Forward current transfer ratio * | h_{FE} | $V_{CE} = -4\text{ V}, I_C = -0.5\text{ A}$ | 300 | | 700 | |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -2\text{ A}, I_B = -0.05\text{ A}$ | | | -1 | V |
| Transition frequency | f_T | $V_{CE} = -12\text{ V}, I_C = -0.2\text{ A}, f = 10\text{ MHz}$ | | 30 | | MHz |

Note) *: Rank classification

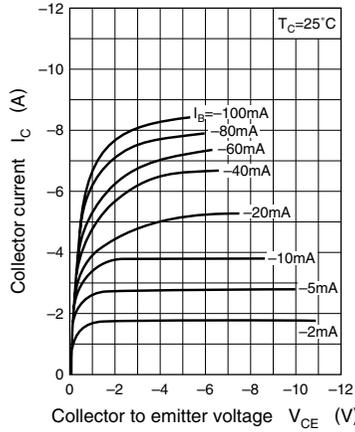
| Rank | Q | P |
|----------|------------|------------|
| h_{FE} | 300 to 500 | 400 to 700 |



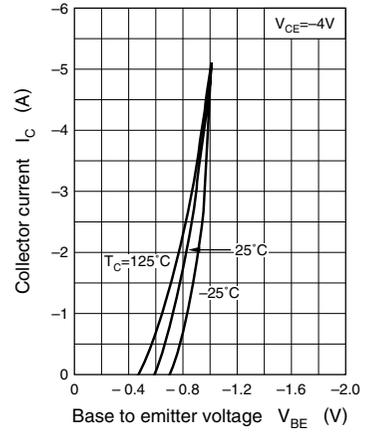
$P_C - T_a$



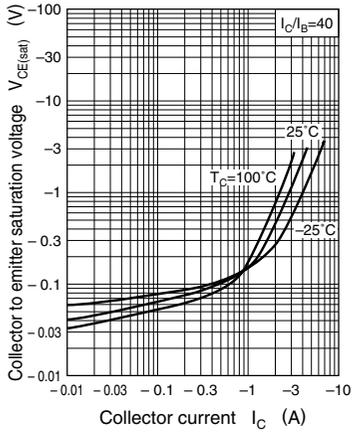
$I_C - V_{CE}$



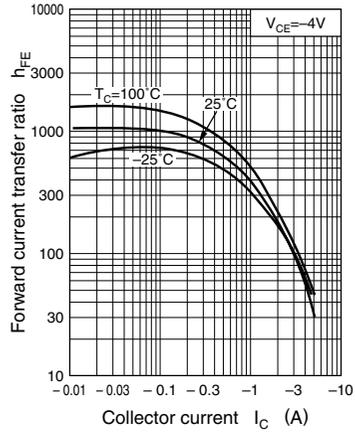
$I_C - V_{BE}$



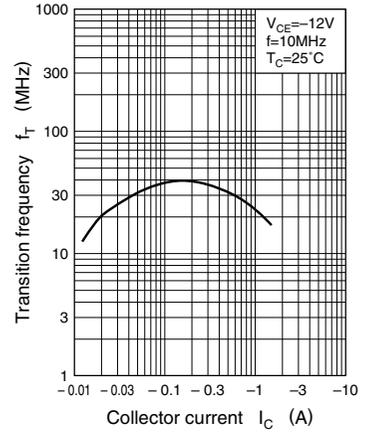
$V_{CE(sat)} - I_C$



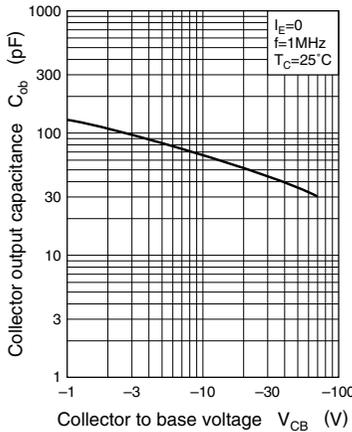
$h_{FE} - I_C$



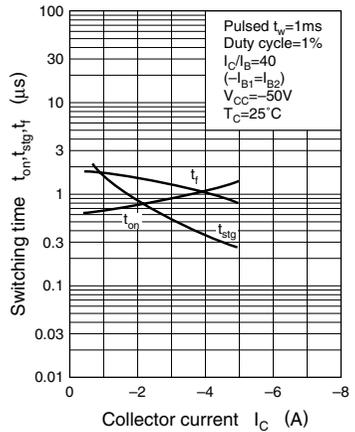
$f_T - I_C$



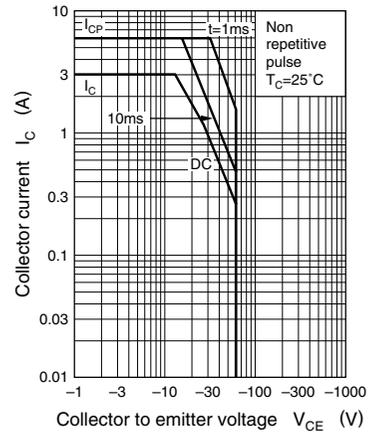
$C_{ob} - V_{CB}$



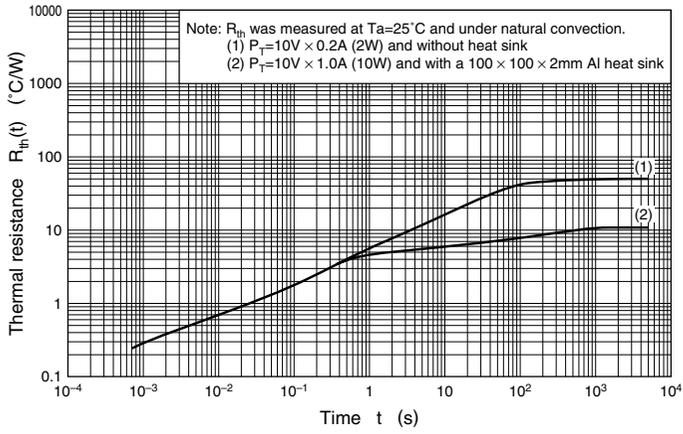
$t_{on}, t_{stg}, t_f - I_C$



Area of safe operation (ASO)



$$R_{th(t)} - t$$



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